

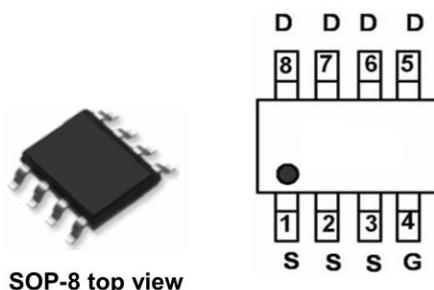
## GENERAL FEATURES

- $V_{DS} = 30V, I_D = 12A$
- $R_{DS(ON)} < 12m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} < 16m\Omega @ V_{GS}=4.5V$

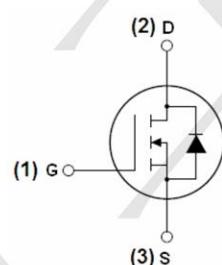
## Application

- Battery protection
- Load switch

## Package and Pin Configuration



## Circuit diagram



## Marking:



## Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	12	A
Drain Current-Continuous( $T_c=100^\circ C$ )	$I_D (100^\circ C)$	6	A
Pulsed Drain Current	$I_{DM}$	50	A
Maximum Power Dissipation	$P_D$	2.5	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

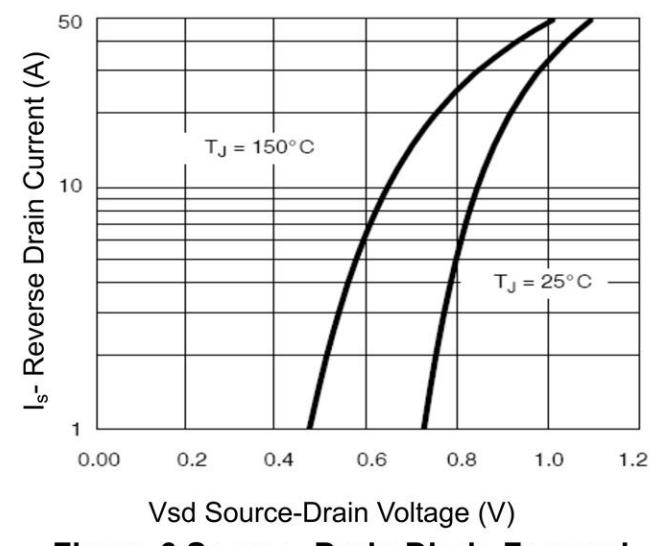
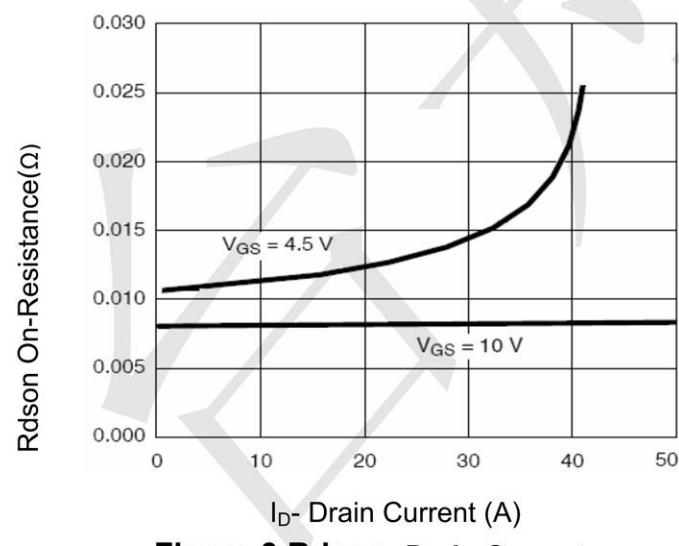
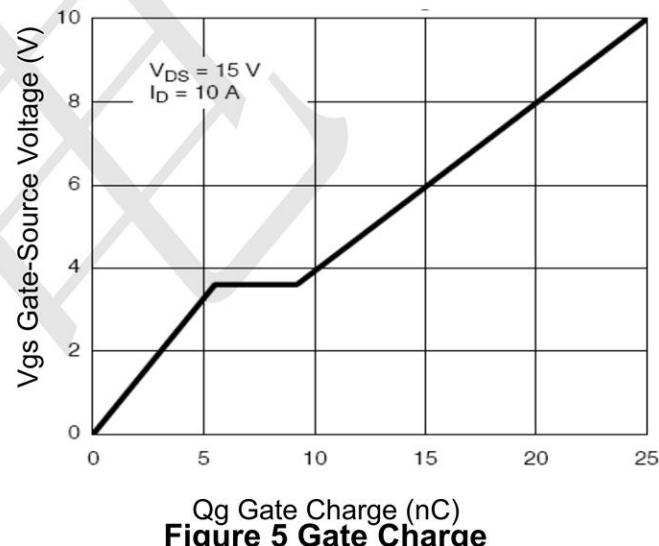
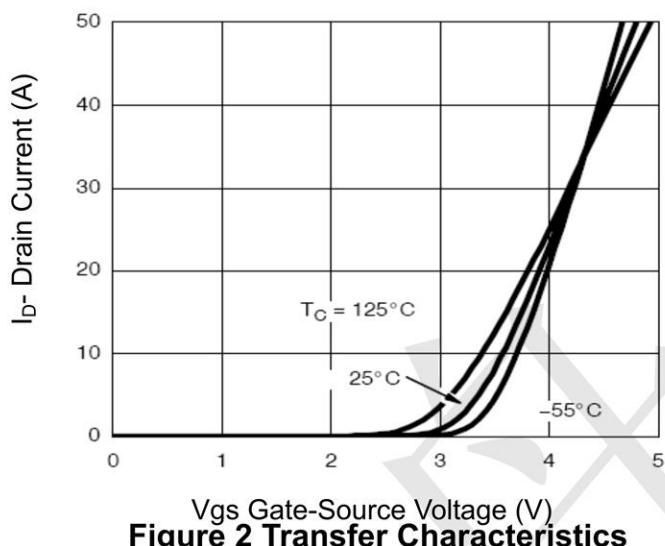
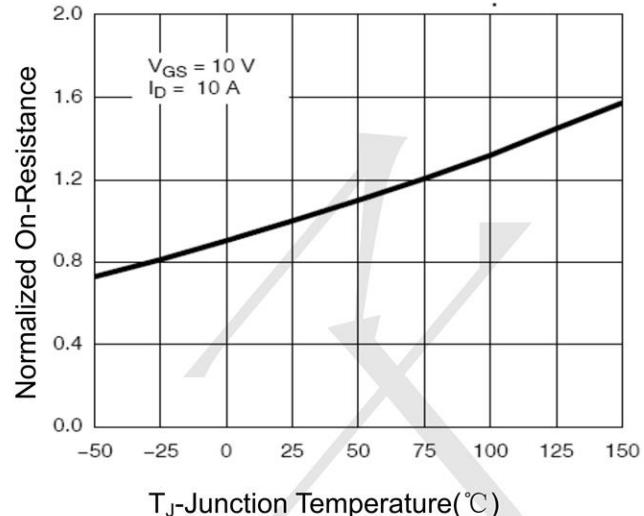
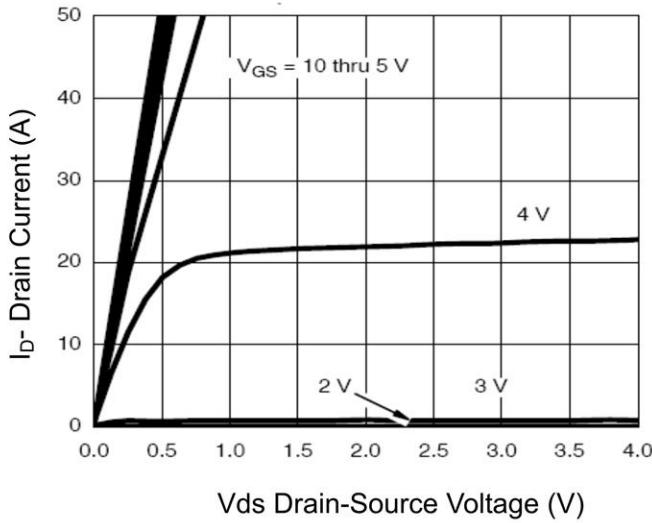
## Thermal Characteristic

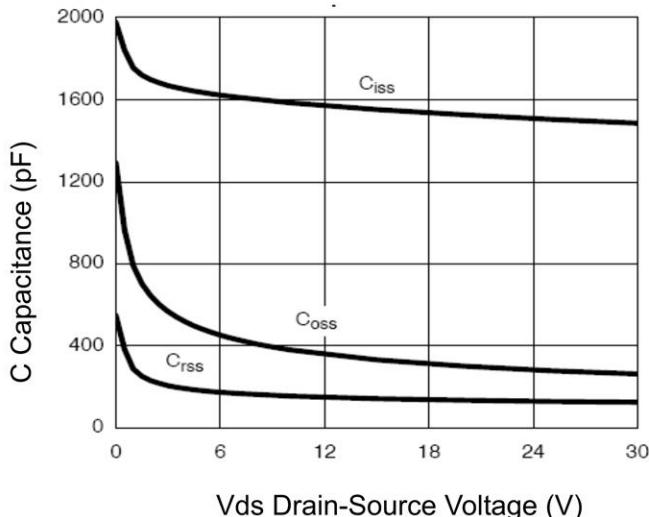
Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	50	°C/W
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**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

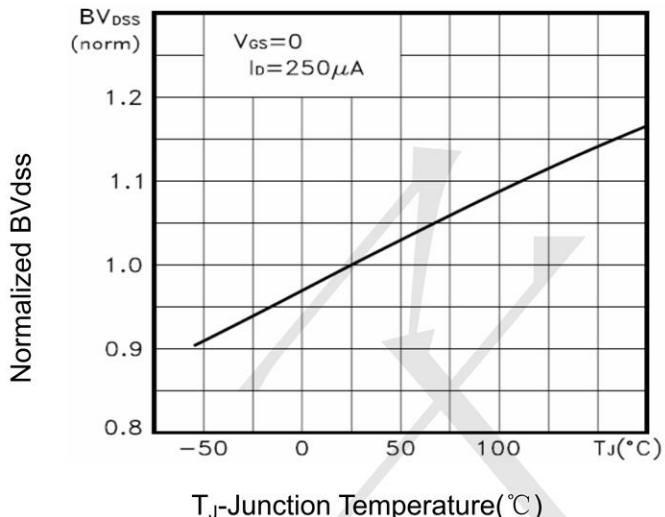
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	30	-	-	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics</b> <small>(Note 3)</small>						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1	1.6	3	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=10\text{A}$	-	8	12	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=8\text{A}$	-	11	16	
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}}=5\text{V}, I_{\text{D}}=10\text{A}$	15	-	-	S
<b>Dynamic Characteristics</b> <small>(Note 4)</small>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	1550	-	PF
Output Capacitance	$C_{\text{oss}}$		-	300	-	PF
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	180	-	PF
<b>Switching Characteristics</b> <small>(Note 4)</small>						
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=25\text{V}, I_{\text{D}}=1\text{A}$ $V_{\text{GS}}=10\text{V}, R_{\text{GEN}}=6\Omega$	-	30	-	nS
Turn-on Rise Time	$t_r$		-	20	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	100	-	nS
Turn-Off Fall Time	$t_f$		-	80	-	nS
Total Gate Charge	$Q_g$	$V_{\text{DS}}=15\text{V}, I_{\text{D}}=10\text{A}, V_{\text{GS}}=5\text{V}$	-	13	-	nC
Gate-Source Charge	$Q_{\text{gs}}$		-	5.5	-	nC
Gate-Drain Charge	$Q_{\text{gd}}$		-	3.5	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <small>(Note 3)</small>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_{\text{s}}=10\text{A}$	-	-	1.2	V
Diode Forward Current <small>(Note 2)</small>	$I_{\text{s}}$		-	-	12	A

**Typical Electrical and Thermal Characteristics (Curves)**

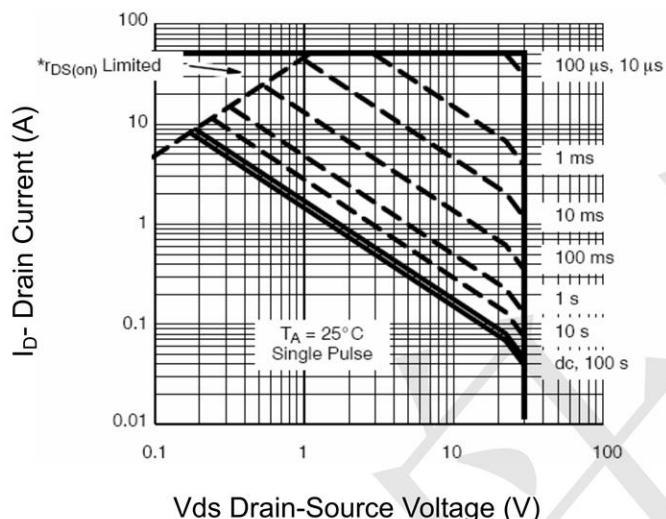




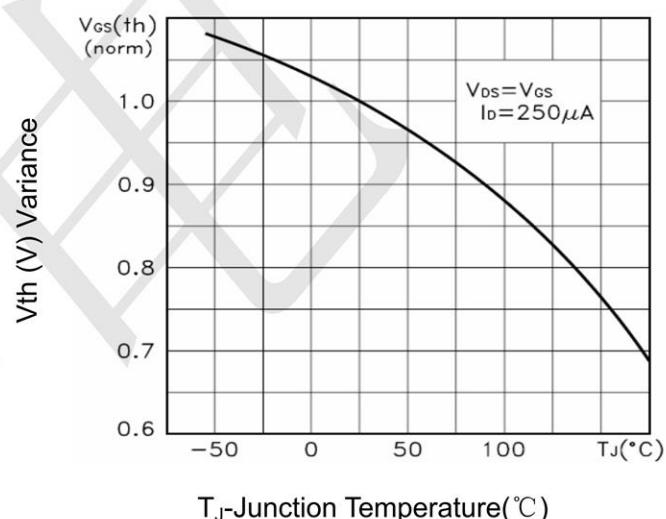
**Figure 7 Capacitance vs Vds**



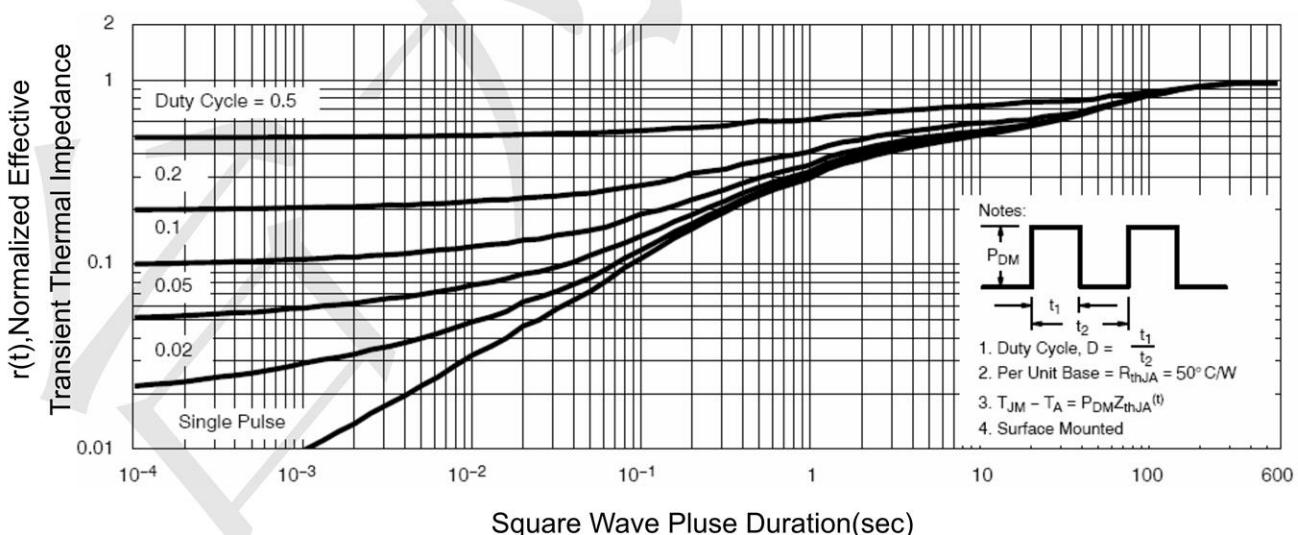
**Figure 9  $BV_{DSS}$  vs Junction Temperature**



**Figure 8 Safe Operation Area**



**Figure 10  $V_{GS(th)}$  vs Junction Temperature**



**Figure 11 Normalized Maximum Transient Thermal Impedance**



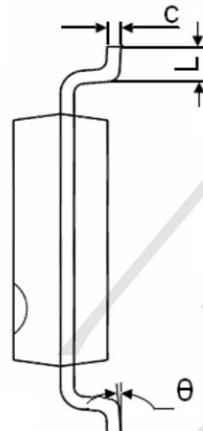
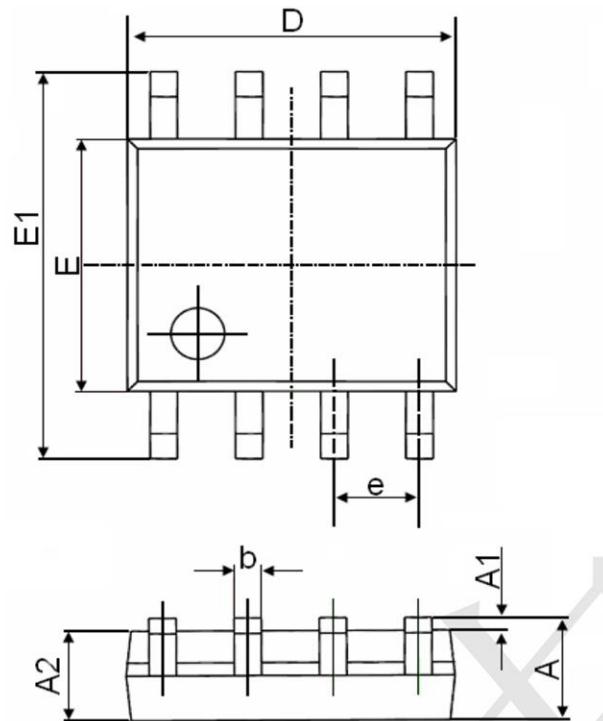
**TECH PUBLIC**  
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**IRF7807**

N-Channel Enhancement Mode Power MOSFET

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### SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°